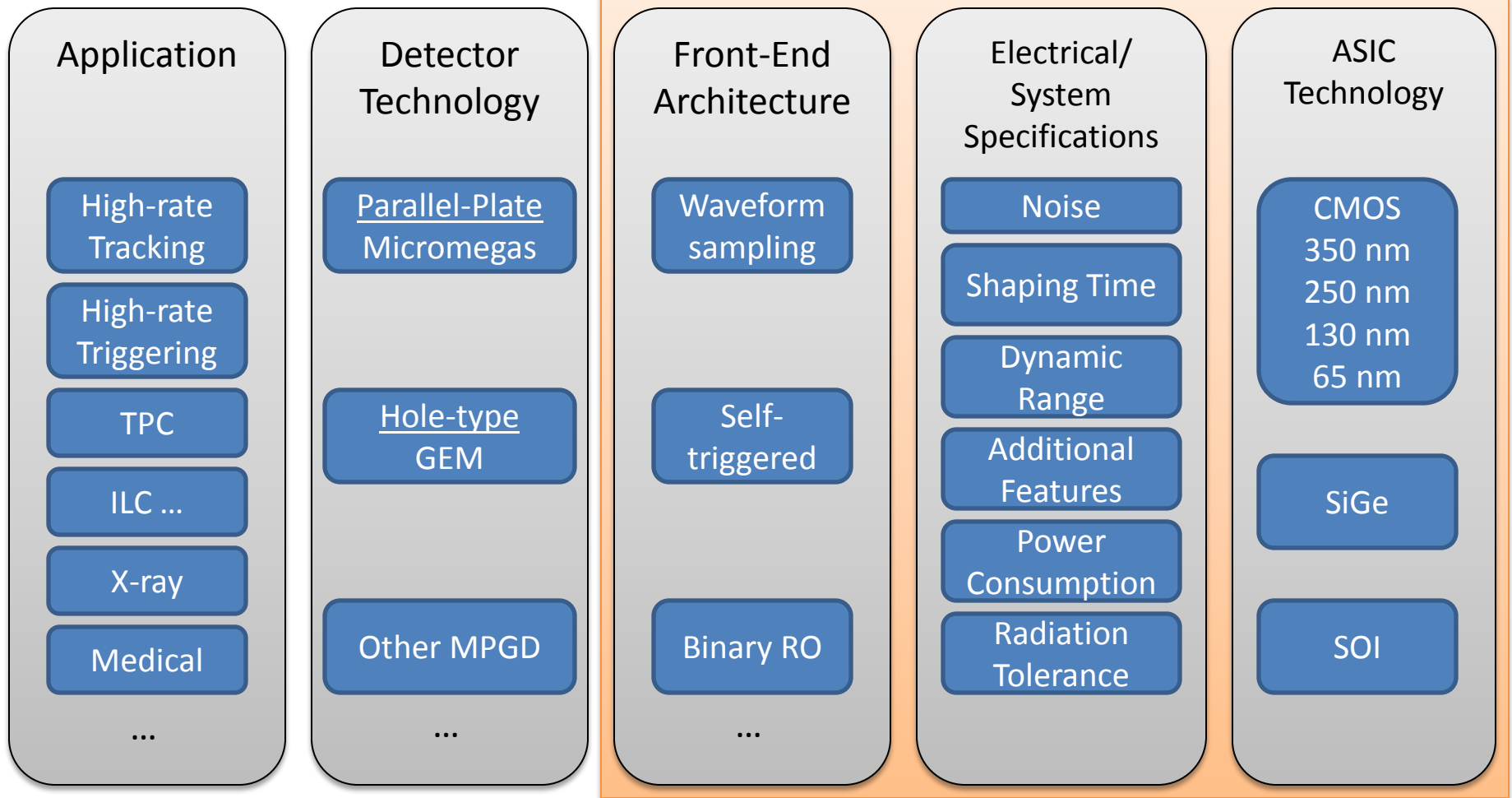


# From Chip Matrix to the 'Ideal Chip' for MPGD

Sorin Martoiu, CERN PH/DT

# “Ideal Chip” Specification



# Applications

## Application

High-rate  
Tracking

High-rate  
Triggering

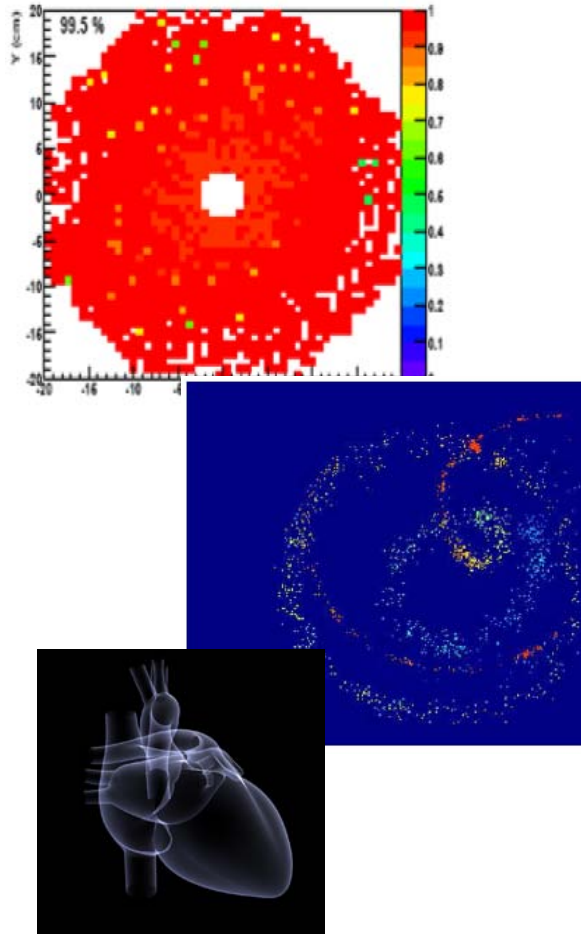
TPC

ILC ...

X-ray

Medical

...



- total rate = ... 25 kHz/mm<sup>2</sup>
- rate/channel = ?
- spatial resolution = 10 ... 100 um
- temporal resolution = 1 .. 25 ns
- energy resolution = ?
- efficiency = 95 ... 99 %

# Detectors

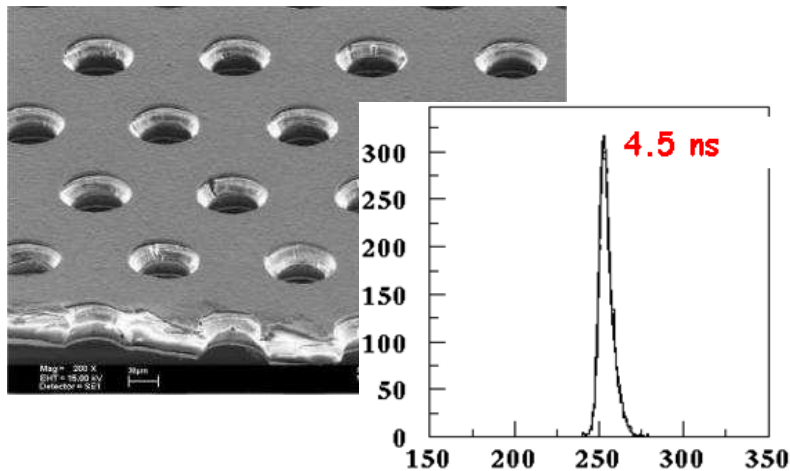
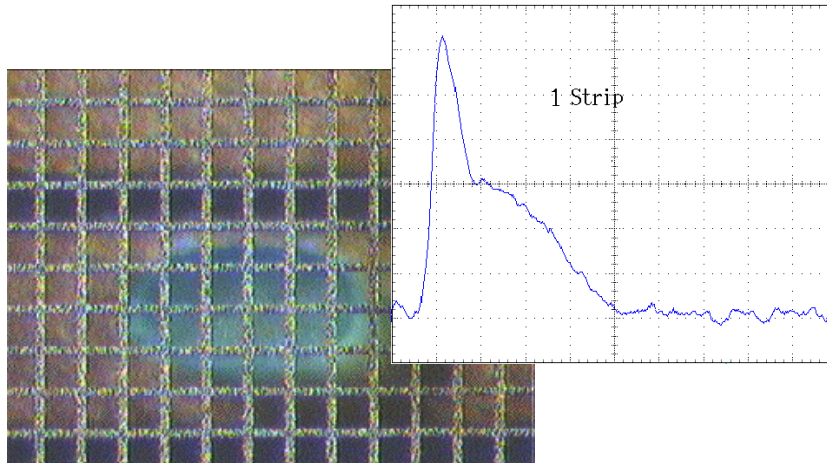
## Detector Technology

Parallel-Plate  
Micromegas

Hole-type  
GEM

Other MPGD

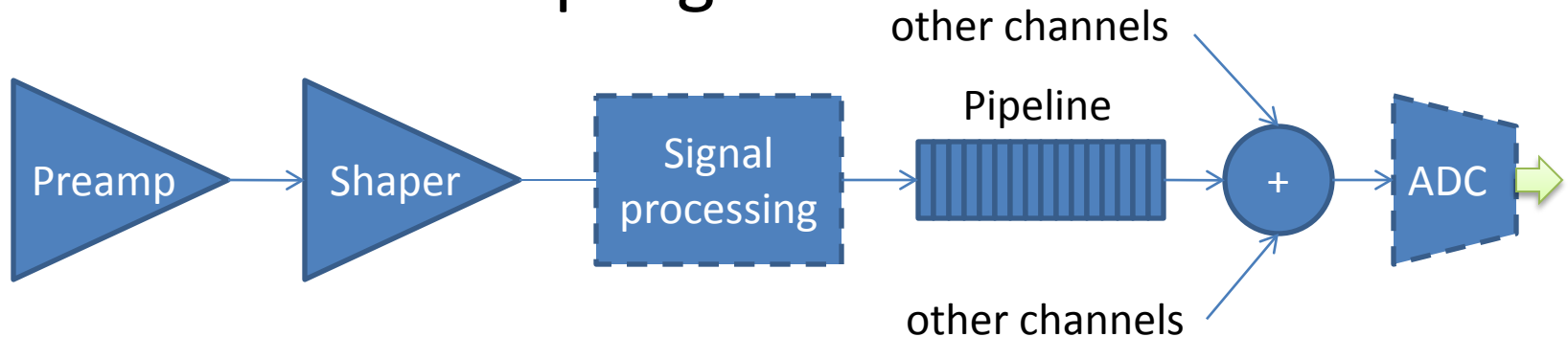
...



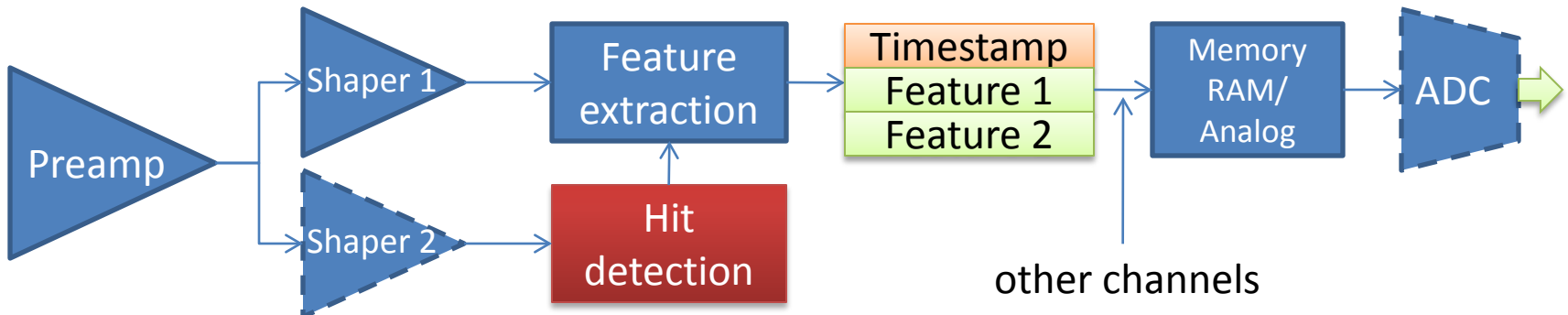
- gas gain =  $10^3 \dots 10^5$
- signal range = 10 .. 1000 ke<sup>-</sup>
- amplitude distribution
- signal width = 5 .. 20ns

# Front-End Architecture

- Waveform sampling



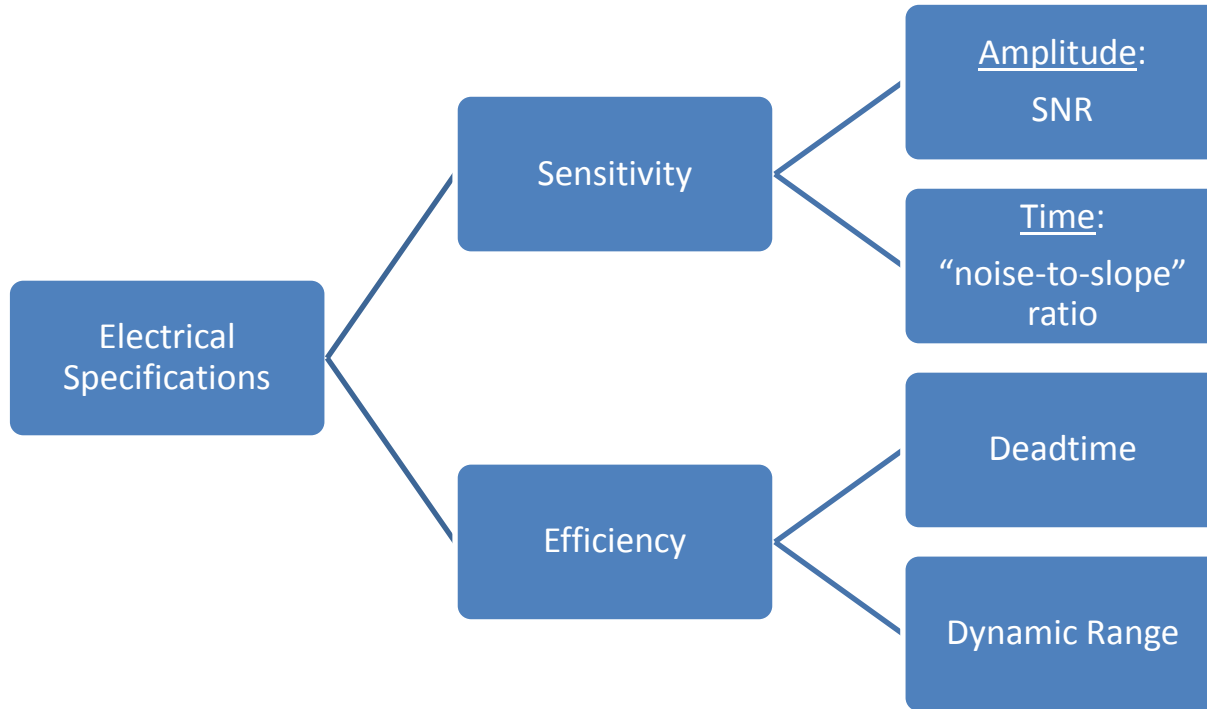
- Self-triggered channel



# Front-End Architecture

	Pros	Cons
<p><b>Waveform sampling</b></p> <ul style="list-style-type: none"> <li>• analog: <i>APV25, Beetle</i></li> <li>• binary: <i>VFAT</i></li> <li>• digital: <i>(S)ALTRO, SVX4</i></li> </ul>	<ul style="list-style-type: none"> <li>• simple (relatively)</li> <li>• versatile</li> <li>• off-line data processing               <ul style="list-style-type: none"> <li>• pile-up rejection/detection</li> <li>• systematic error correction</li> <li>• advanced feature extraction</li> </ul> </li> <li>• data rate <math>\sim</math> trigger rate</li> </ul>	<ul style="list-style-type: none"> <li>• high data/event</li> <li>• readout time</li> <li>• needs external trigger</li> <li>• no zero-suppression</li> </ul>
<p><b>Self-triggered channel</b> <i>Example: MSGCROC</i></p>	<ul style="list-style-type: none"> <li>• zero-suppression</li> <li>• optimal data/event</li> </ul>	<ul style="list-style-type: none"> <li>• less versatile               <ul style="list-style-type: none"> <li>• pile-up rejection difficult</li> <li>• limited off-line processing</li> </ul> </li> <li>• data rate <math>\sim</math> event rate</li> <li>• high R/O bandwidth</li> </ul>

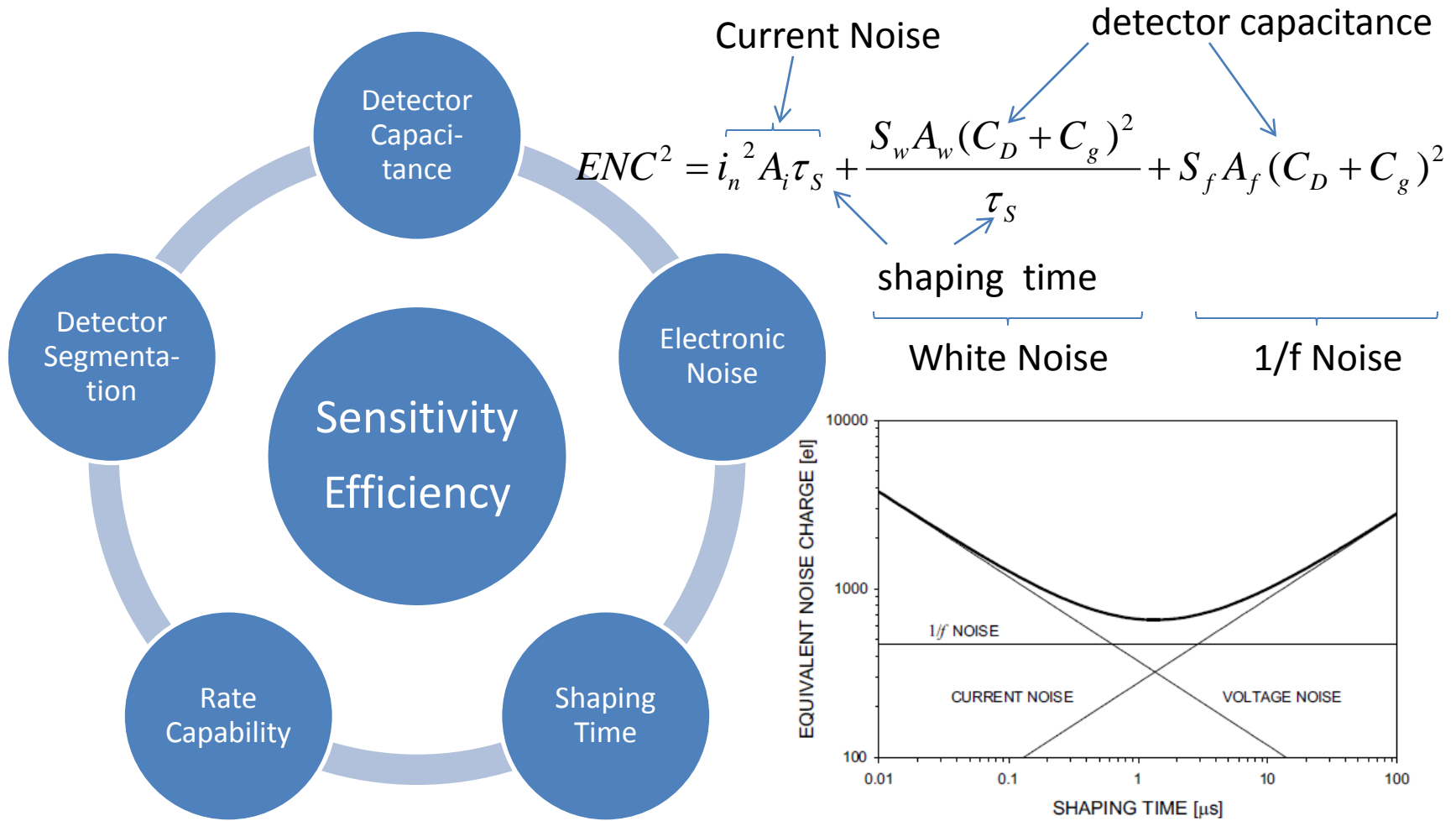
# Electrical Specifications



$$\frac{\Delta E}{E} \propto SNR$$

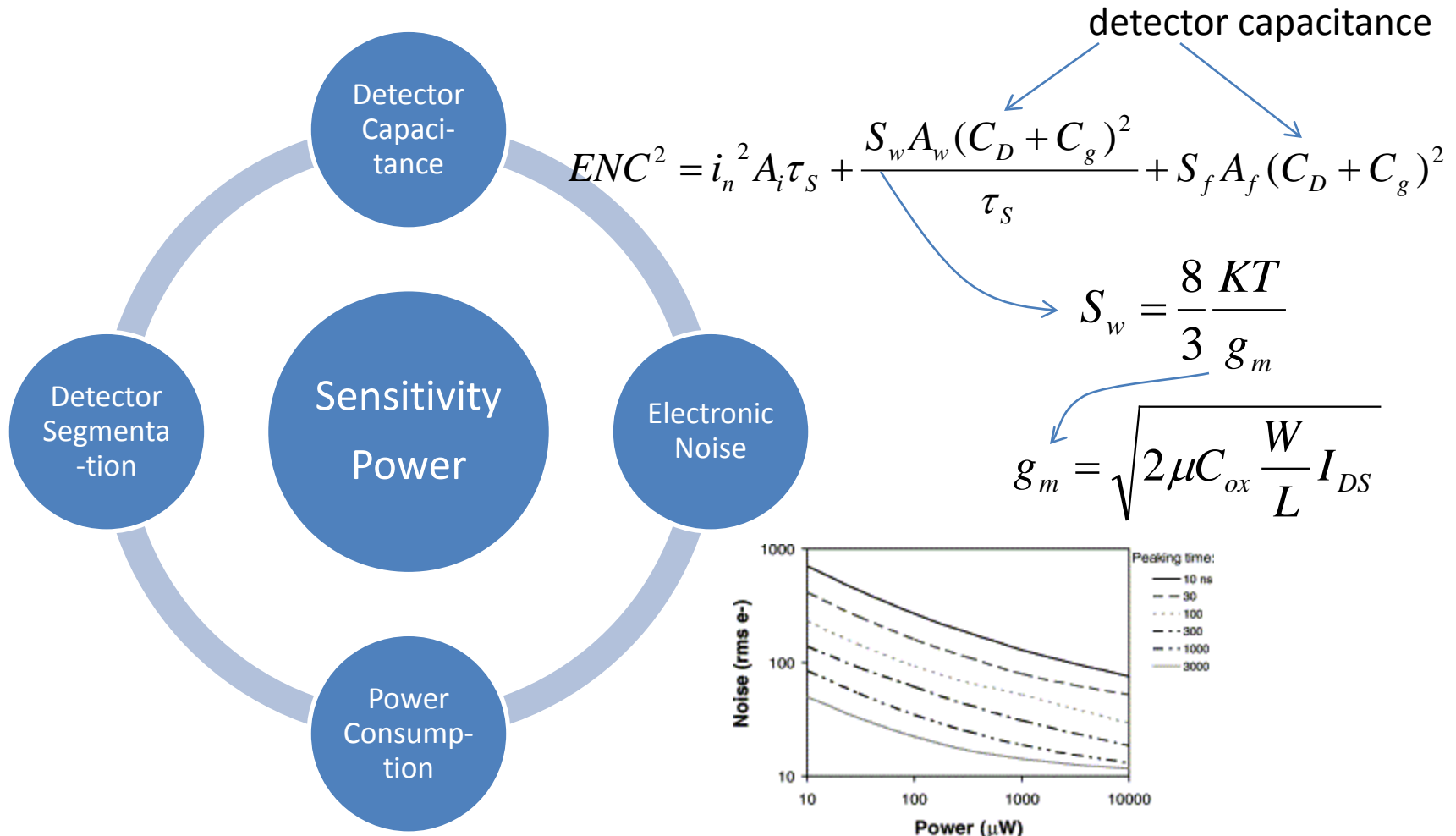
$$\sigma_t = \frac{\sigma_v}{dV/dt}$$

# Sensitivity vs. Efficiency





# Sensitivity vs. Power



# Capacitive Matching

- 1/f noise dominant

$$ENC_{1/f}^2 = A_f K_f \frac{(C_D + C_g)^2}{C_g^2} \quad \Rightarrow \quad C_g = C_D$$

- white noise dominant

$$ENC_w^2 = \frac{8 KTA_w}{3 \tau_s} \sqrt{\frac{L^2}{2\mu}} \frac{(C_D + C_g)^2}{\sqrt{C_g}} \quad \Rightarrow \quad C_g = C_D/3$$

- No preamplifier can provide optimum noise performance for every detector

# Technology

## CMOS scaling

- better noise performance
- lower dynamic range
- optimum technology for analog design appears to be around the 0.25 $\mu\text{m}$  node

## Digital circuits clearly benefit from scaling

- Smaller ADCs
- More powerful digital signal processing
- (Auto)calibration and error correction digital circuits could compensate the analog performance deficit

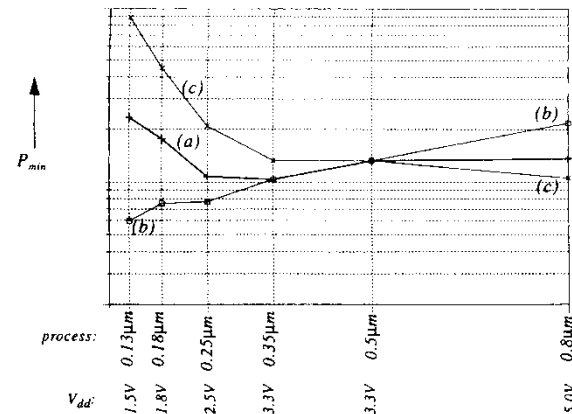
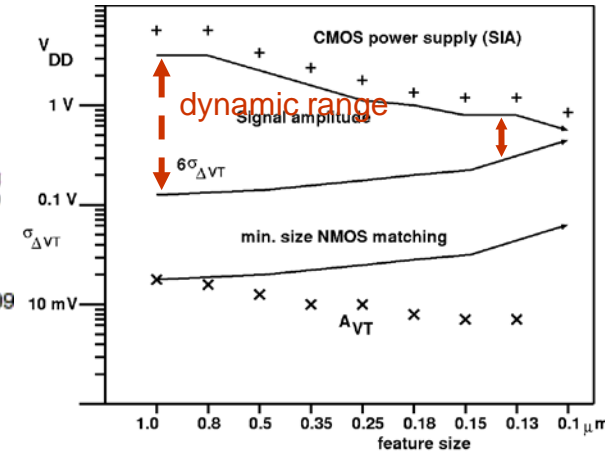
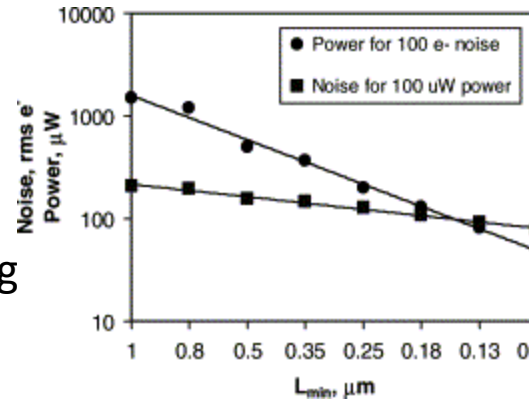


Fig. 8. Minimum power consumption for a voltage follower circuit (with constant topology, SINAD and maximum signal frequency). (a) Made in various processes, operated at their corresponding supply voltages. (b) Made in various processes, all operated at  $V_{dd} = 3.3$  V. (c) All made in 0.5- $\mu\text{m}$  CMOS, operated at various supply voltages.

# Features

## Chip matrix

Name	Exp	Det	#ch	Shaper (ns)	Noise	Range (fC)	Pol.	ADC	f (MHz)	P/ch. (mW)	Feat.	Tech	Rad hard
APV25	CMS	Si strip	128	50	270+38e/pF	20	both	A	40	2.7	PD, PR	0.25 CMOS	10
AFTER	T2K	TPC	72	100-2000	(350-1800) + s-gauss	19	both	A	1-50 (100)	7.5	VG, VS	0.35 CMOS	no
MSGCROC	DETNI	Gas strip	32	T: 25 E: 85	2000e @ 40pF	800	both	A,1	2ns TDC		VG, ZS	0.35 CMOS	no
Beetle	LHCb		128	25	500+50e/pF	17.5	both	A/1	40	5.2	F-OR	0.25 CMOS	40
VFAT	TOTEM		128	22	650+50e/pF	18.5 (cal)	both	1	40	4.47	F-OR	0.25 CMOS	50
NINO	ALICE	TPC	8	1	1900+165/pF	2000 th<100	both	1	async	30	BR	0.25 CMOS	no
CARIOCA	LHCb	MWPC	8	<15 @ 220pF	2000+40e/pF	250	both	1	async	46	BR	0.25 CMOS	20
PASA+ALTRO	ALICE TPC	TPC	16	190 <sub>fwhm</sub> s-gauss	570e @20 pF	160	both	10	20	< 40	BC, TC, ZS	0.35, 0.25 CMOS	
SVX4	CDF, D0	Si strip	128	100-360	410+45e/pF	60fC	neg	8	106 (212)	2	ZS	0.25 CMOS	20
SPIROC	ILC, T2K	SiPM	36	A:25-175 T:10	A: 1/11pe; T:1/24pe	2000 pe	neg	8-12	100ps TDC	0.025 pulse	dual-gain	0.35 SiGe	no

Legend: PD = peak detection, PR = pile-up rejection, VG = variable gain, VS = variable shaping, F-OR = fast-OR, BR = baseline restorer, BC = baseline correction, TC = tail correction, DC = data compression, ZS = zero suppression

- ✓ fast-OR,
- ✓ variable gain,
- ✓ variable shaping,
- ✓ peak detection
- ✓ pile-up rejection,
- ✓ baseline restorer,
- ✓ baseline correction,
- ✓ tail correction,
- ✓ data compression,
- ✓ zero suppression

# From Chip Matrix to the Ideal Chip

Name	Exp	Det	#ch	Shaper (ns)	Noise	Range (fC)	Pol.	ADC	f (MHz)	P/ch. (mW)	Feat.	Tech	Rad hard
APV25	CMS	Si strip	128	50	270+38e/pF	20	both	A	40	2.7	PD, PR	0.25 CMOS	10
AFTER	T2K	TPC	72	100-2000 s-gauss	(350-1800)+(22-1.8)e/pF	19	both	A	1-50 (100)	7.5	VG, VS	0.35 CMOS	no
MSGCROC	DETNI	Gas strip	32	T: 25 E: 85	2000e @ 40pF	800	both	A,1	2ns TDC		VG, ZS	0.35 CMOS	no
Beetle	LHCb		128	25	500+50e/pF	17.5	both	A/1	40	5.2	F-OR	0.25 CMOS	40
VFAT	TOTEM		128	22	650+50e/pF	18.5 (cal)	both	1	40	4.47	F-OR	0.25 CMOS	50
NINO	ALICE	TPC	8	1	1900+165/pF	2000 th<100	both	1	async	30	BR	0.25 CMOS	no
CARIOCA	LHCb	MWPC	8	<15 @ 220pF	2000+40e/pF	250	both	1	async	46	BR	0.25 CMOS	20
PASA+ ALTRO	ALICE TPC	TPC	16	190 <sub>fwhm</sub> s-gauss	570e @ 20 pF	160	both	10	20	< 40	BC, TC, ZS	0.35, 0.25 CMOS	
SVX4	CDF, DO	Si strip	128	100-360	410+45e/pF	60fC	neg	8	106 (212)	2	ZS	0.25 CMOS	20
SPIROC	ILC, T2K	SiPM	36	A: 25-175 T: 10	A: 1/11pe; T: 1/24pe	2000 pe	neg	8-12	100ps TDC	0.025 pulse	dual-gain	0.35 SiGe	no

Legend: PD = peak detection, PR = pile-up rejection, VG = variable gain, VS = variable shaping, F-OR = fast-OR, BR = baseline restorer, BC = baseline correction, TC = tail correction, DC = data compression, ZS = zero suppression

- shaping time: 5ns .. 1us
- dynamic range: <100fC
- power: < 10 mW/ch (?)
- ADC accuracy: 10 bits (?)
- TDC accuracy: 1ns

...

We need an **APV25** chip with variable gain and shaping time like the AFTER chip, dynamic range like MSGCROC, integrated fast-OR like Beetle, integrated ADC like SVX4, digital signal processor like ALTRO